

## LITERATURA

- [1] Frank, H. - Šnejdar, V.: Principy a vlastnosti polovodičových součástek. Praha: SNTL 1976.
- [2] Graff de, H. C. - Klaasen, F. M.: Compact Transistor Modeling for Circuit Design. Wien: Springer Verlag 1990.
- [3] Kubát, M.: Výkonová polovodičová technika. Praha: SNTL 1978.
- [4] Sze, S.M.: Physics of Semiconductor Devices. New York: John Wiley & Sons 1981.
- [5] Selberherr, S.: Analysis and simulation of Semiconductor devices. Wien: Springer Verlag 1984.
- [6] Hunter, L.R.: Handbook of Semiconductor Electronics. New York: McGraw Hill 1970.
- [7] Muller, R.S. - Kamins, T.I.: Device electronics for integrated circuits. New York: John Wiley & Sons 1977.
- [8] Sedra, A.S. - Smith, K.C.: Microelectronic Circuits. Philadelphia: Saunders College Publishing 1992.
- [9] Leach, D.P.: Discrete and Integrate Circuit Electronics. New York: Saunders College Publishing 1992.
- [10] Millman, J. - Grabel, A.: Microelectronics. New York: McGraw Hill Book Company 1988.
- [11] Hamilton, D.J. - Howard, W.G.: Basic Integrated Circuit Engineering. New York: McGraw Hill 1975.
- [12] Geiger, R.L. - Allen, P.E. - Strader, N.R.: VLSI Design Technique For Analog and Digital Circuits. New York: McGraw Hill 1990.
- [13] Allen, P.E. - Holberg, D.R.: CMOS Analog Circuits Design. Fort Worth: Holt, Rinehart and Winston, Inc. 1987.
- [14] Grey, P.R. - Meyer, R.G.: Analysis and Design of Analog Integrated Circuits. New York: John Wiley & Sons 1977, 1984.
- [15] Warner, R.M. - Grung, B.L.: Transistors Fundamentals for the Integrated - Circuit Engineer. New York: John Wiley & Sons 1983.
- [16] Kurata, M.: Numerical Analysis for Semiconductor Devices. Toronto: Lexington Books 1982.
- [17] Trutko, A.F.: Metody rasčota tranzistorov. Moskva: Energija 1971.
- [18] Marciniak, W.: Modele elementov polprzewodnikowych. Warszawa: Wydawnictwo Naukowo-Techniczne 1985.
- [19] Getreu, J.E.: Modeling the Bipolar Tranzistor. Amsterdam: Elsevier 1978.
- [20] Stěpaněňko, J.P.: Osnovy teorii tranzistorov i tranzistornych schem. Moskva: Energija 1977.
- [21] Pasyňkov, V.V. - Čirkin, L.K.: Poluprovodnikovyje pribory. Moskva: Vyššaja škola 1987.
- [22] Vaníček, F.: Modely elektronických struktur. Praha: Ediční středisko ČVUT 1992.
- [23] Spiridonov, N.S.: Osnovy teorii tranzistorov. Kijev: Technika 1975.

- [24] Rževkin, K.S.: Fizičeskije principy dejstvija poluproduktivnyh priborov. Moskva: Izdatel'stvo Moskovskovo Universiteta 1986.
- [25] Fibich, Z. a kol.: Křemíkové vysokofrekvenční tranzistory. Praha: SNTL 1984.
- [26] Streetman, B.G.: Solid State Elektron Devices. London: Prentice Hall 1972.
- [27] Till, W.C. - Luxon, J.T.: Integrated Circuits: materials, devices and fabrication. Englewood Cliffs 1972.
- [28] Marciniak, W. : Polovodičové součástky typu MIS. Praha: SNTL 1979.
- [29] Grove, A.S.: Physics and Technology of Semiconductor Devices. New York: John Wiley & Sons 1967.
- [30] Suguno, T.- Ikoma, T. - Takeisi, E. : Vvedenie v mikroelektroniku. Moskva: Mir 1988. Překlad z japonštiny.
- [31] Frank, H.: Fyzika a technika polovodičů. Praha: SNTL 1990.
- [32] Šalimova, K. V.: Fizika poluprovodnikov. Moskva: Energija 1976.
- [33] Yang, E.S.: Fundamentals of Semiconductor Devices. New York: McGraw Hill 1978.
- [34] Ghandhi, S.K.: Semiconductor Power Devices. New York: John Wiley & Sons 1977.
- [35] Lindmayer, J. - Wrigley, Ch.Y.: Fundamentals of Semiconductor Devices. New York: D. van Nostrand Company 1965.
- [36] Oxner, E. S.: FET Technology and Application. An Introduction. New York: Marcel Dekker, Inc. 1989.
- [37] Kobbold, R.: Teorija i primenjenje polevyh tranzistorov. Leningrad: Energija 1975.
- [38] Ričman, P.: Fizičeskije osnovy polevyh tranzistorov s izolirovannym zatvorom. Moskva: Sovetskoje radio 1971.
- [39] Ignatov, A.N.: Polevyje tranzistory i ich primenjenje. Moskva: Radio i svjaz 1984.
- [40] Katalogy firmy Motorola: Small signal tranzistors, FETs and diode device data.
- [41] Levinštejn, M.E. - Simin, G.S.: Barjery. Ot kristala do intěgralnoj schemy. Moskva: Nauka 1987.
- [42] Wood, D.: Optoelectronic Semiconductor Devices. New York: Prentice Hall 1994.
- [43] Zíka, J.: Diody a tyristory v průmyslové elektronice. Praha: SNTL 1979.
- [44] Ladbroke, P.H.: MMIC Design GaAs FET and HEMTs. Boston: Artech House 1989.
- [45] Long, S.I. - Butnet, S.E.: Gallium arsenide digital integrated circuit design. New York: McGraw-Hill 1990.
- [46] Antognetti, P. - Massobrio, G.: Semiconductor device modeling with SPICE. New York: McGraw Hill 1988.

- [47] Laker, R.K.-Sansen, W.M.C.: Design of analog integrated circuits and systems. New York: McGraw-Hill 1994.
- [48] Bronštenjn, J.N. - Semendjajev, K.A.: Spravočnik po matematike. Moskva: GITTL 1956.
- [49] Grant, D.A.-Gowar, J.: Power MOSFETs. Theory and Applications. New York: John Wiley & Sons 1989.
- [50] Antognetti, P.: Power integrated circuits: Physics, Design, and Applications. New York: McGraw-Hill 1986.
- [51] Allison, J.: Electronic engineering materials and devices. London: McGraw-Hill 1971.
- [52] Tuinenga, P.W.: SPICE. A Guide to Circuit Simulation & Analysis Using PSpice. Englewood Cliffs: Prentice Hall 1990.
- [53] Rashid, M.H.: SPICE for Circuits and Electronics Using PSpice. Englewood Cliffs: Prentice Hall 1990.
- [54] Roulston, D.J.: Bipolar Semiconductor Devices. New York: McGraw Hill 1990.
- [55] Angelo, E.J.: Electronics: BJTs, FETs, and Microcircuits. New York: McGraw Hill 1961.
- [56] Cadence SPICE Reference Manual.
- [57] Ignatov, A.N.: Polevye tranzistory i ich primenenie. Moskva: Radio i svjaz 1984
- [58] Ashburn, P.: Design and realization of bipolar transistors. New York: John Wiley & sons 1988.
- [59] Price, T.E.: Introduction to VLSI Technology. New York: Prentice Hall 1994.
- [60] Douglas-Young, J.: Technician's Guide to Microelectronics. New York: Parker Publishing Company, Inc. 1978.
- [61] Ziel, Adalbert van der: Solid State Physical Electronics. Englewood Cliffs: Prentice Hall 1971.
- [62] Deboo, G.J.-Burrous, C.N.: Integrated Circuits and Semiconductor Devices. Theory and Application. New York: McGraw-Hill Book Company 1971.
- [63] Gosling, W.-Townsend, W.G.-Watson, J.: Field-effect electronics. London: Butterworths 1971.
- [64] Tyagi, M.S.: Introduction to semiconductor materials and devices. New York: John Wiley & Sons 1991.
- [65] Kennedy, D.P.: The Potential and Electric Field at the Metallurgical Boundary of an Abrupt p-n Semiconductor Junction. IEEE Transaction on Electron Devices, vol ED-22 (1975), č. 11, str. 988 až 994.
- [66] Berman, L.S.: Nelinejnaja poluprovodnikovaja emkošć. Moskva: Fizmatgiz 1963.

- [67] Klaassen, D.B.M.: A unified mobility model for device simulation-I. Model equations and concentration dependence. Solid State Electronics, Vol 35 (1992),No.7, pp. 953-959.
- [68] Klaassen, D.B.M.: A unified mobility model for device simulation-II. Temperature dependence of carrier mobility and lifetime. Solid State Electronics Vol 35 (1992),No.7, pp. 961-967.
- [69] Křivohlávek, J.: Jednorozměrný matematický model bipolárního tranzistoru. Slaboproudý Obzor 47 (1986), č.11, 12, str.548 až 554.
- [70] Webster, W.M.: On the Variation of Junction-Transistor Current-Amplification Factor with Emitter Current. Proceedings of the IRE ~~1954~~ June, pp.914-921.
- [71] Přehnal, V.: Křemíková dioda jako teplotní čidlo. Sborník z konference "Měření teploty v chemii". ČSVT Pardubice 1976.
- [72] Prochorov, A.M.a kol.: Fizičeskij enciklopedičeskij slovar. Moskva: Sovetskaja enciklopedija 1984.
- [73] Rothbauer, M. a kol.: Mikrovlnné polovodičové sočástky a jejich použití. Praha: SNTL 1985.